

Point Defect Diffusion

K.G. Field^{1,a},

^akgfield@umich.edu

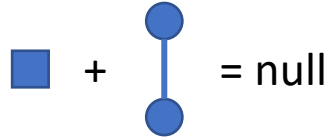
¹University of Michigan



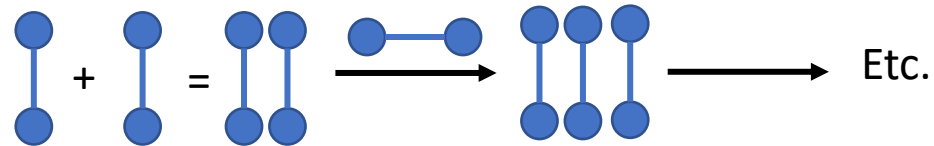
**NUCLEAR ENGINEERING &
RADIOLOGICAL SCIENCES**
UNIVERSITY OF MICHIGAN

What is the fate of point defects?

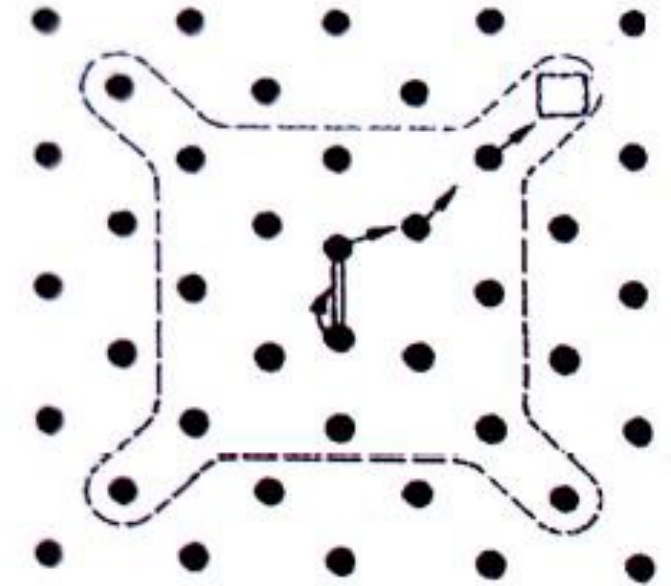
1. Annihilation (recombination)



2. Clustering

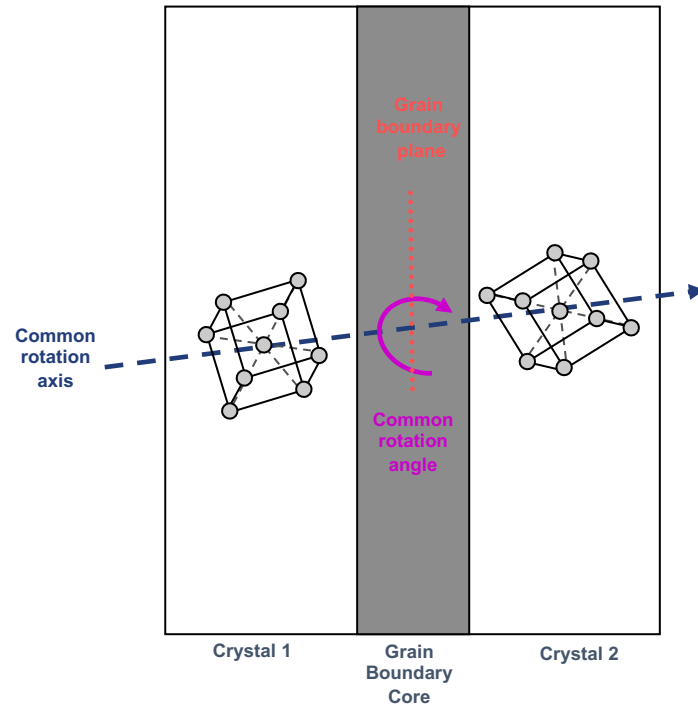


3. Elimination at Sinks

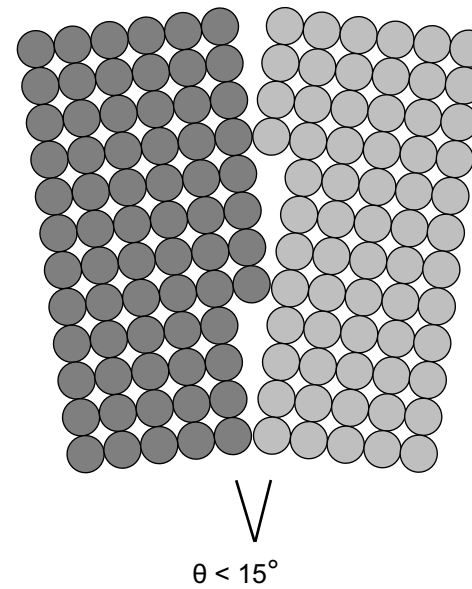


To determine the fate of point defects we need to determine C_v and C_i at any time during the irradiation, which is tied to their formation and migration!

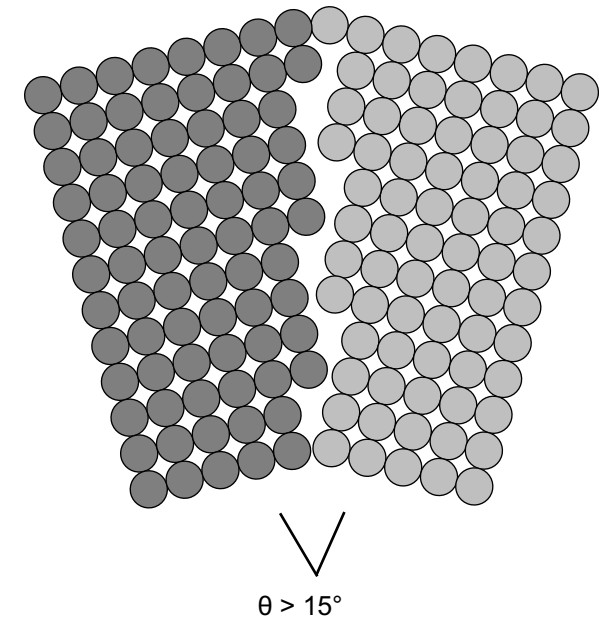
Elimination at Sinks



Low Angle Grain Boundary



High Angle Grain Boundary



Example problem (4.1 in Was) – to make a point

Calculate the concentration of vacancies and interstitials at room temperature for pure Al

$$T = 293 \text{ K}$$

$$E_f^v \approx 0.66 \text{ eV}$$

$$S_f^v \approx 0.7 k_b$$

$$E_f^i \approx 3.2 \text{ eV}$$

$$S_f^i \approx 8 k_b$$

$$C_i = \exp\left(\frac{S_{vib}}{k_b}\right) \exp\left(\frac{-E_i}{k_b T}\right) \quad C_v = \exp\left(\frac{S_{vib}}{k_b}\right) \exp\left(\frac{-E_v}{k_b T}\right)$$

Point defect properties

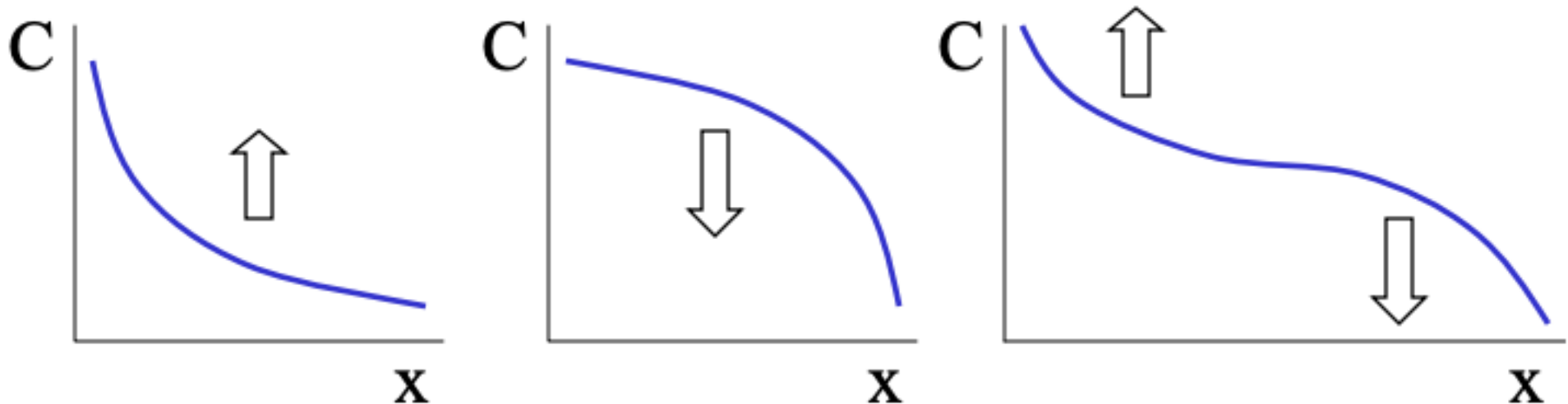
	Symbol	Unit	Al	Cu	Pt	Mo	W
Interstitials							
Relaxation volume	V_{relax}^i	Atomic vol.	1.9	1.4	2.0	1.1	
Formation energy	E_f^i	eV	3.2	2.2	3.5		
Equilibrium concentration at T_m^*	$C_i(T_m)$	-	10^{-18}	10^{-7}	10^{-6}		
Migration energy	E_m^i	eV	0.12	0.12	0.06		0.054
Vacancies							
Relaxation volume	V_{relax}^v	Atomic vol.	0.05	-0.2	-0.4		
Formation energy	E_f^v	eV	0.66	1.27	1.51	3.2	3.8
Formation entropy	S_f^v	k	0.7	2.4			2
Equilibrium concentration at T_m^*	$C_v(T_m)$	-	9×10^{-6}	2×10^{-6}			4×10^{-5}
Migration energy	E_m^v	eV	0.62	0.8	1.43	1.3	1.8
Activation energy for self diffusion	Q_{vSD}	eV	1.28	2.07	2.9	4.5	5.7
Frenkel pairs							
Formation energy	E_f^{FP}	eV	3.9	3.5	5		

Fick's First Law of Diffusion

- Relates the flux and the concentration gradient of the diffusing specie:
- D is given in cm^2/s or m^2/s
- For solids it is between 20-1500°C, $10^{-20} < D < 10^{-4} \text{ cm}^2/\text{s}$

Fick's Second Law of Diffusion

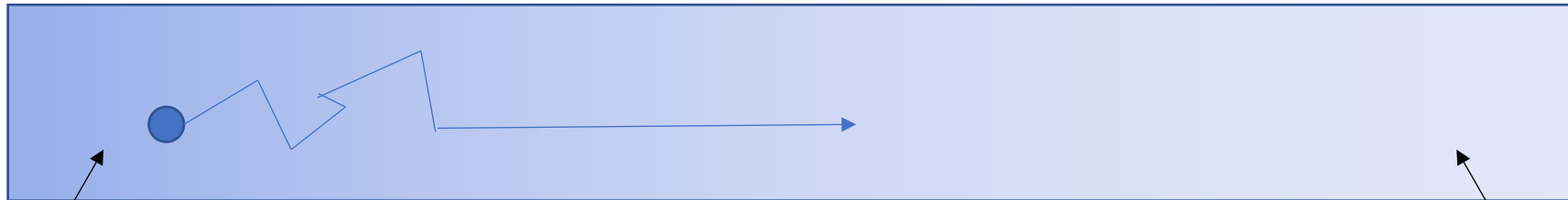
- Provides the relationship between the concentration gradient and the rate of change of concentration caused by diffusion at a given point in the system



Fick's First Law of Diffusion

$$J = -D \frac{\partial C}{\partial x}$$

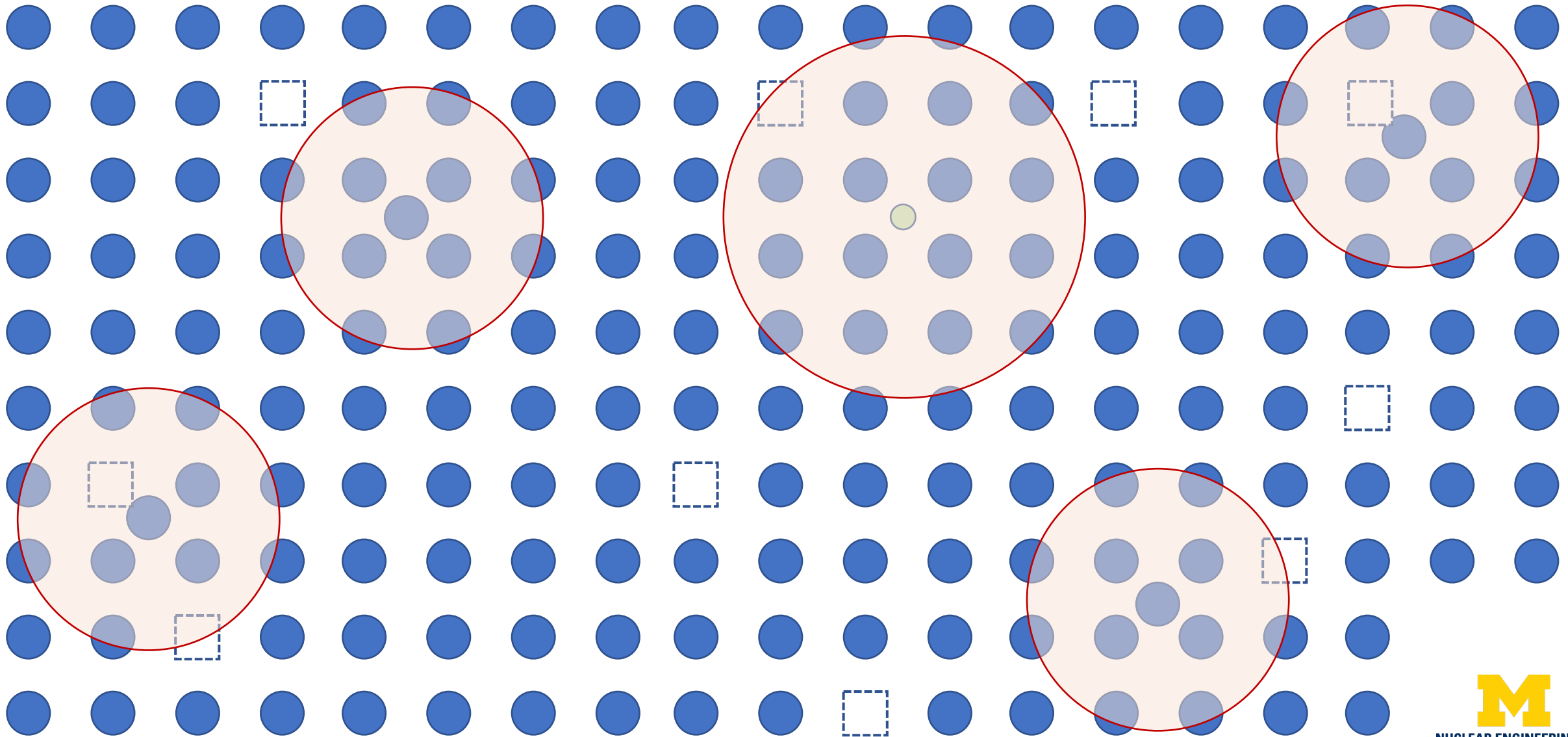
Why do random jumps of atoms result in a net flux of atoms from regions of high concentration towards regions of low concentrations?



Atoms here jump randomly
both right to left

But there are not many
atoms here to jump to the left

Point Defect Migration



How do defect move?

- The defect mobility depends a lot on the defect structure
 - Hence, talking about this is detail last lecture!
- For vacancies, usually a simple jump from one atomic lattice site to another
- For dumbbell interstitials this more complex:

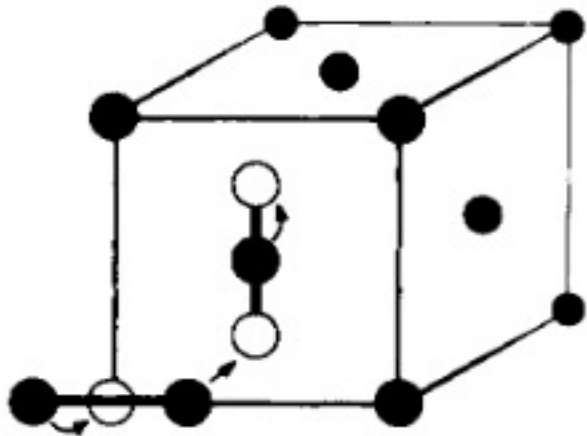


Fig. 4. Migration of the (100)-split interstitial in an fcc lattice.

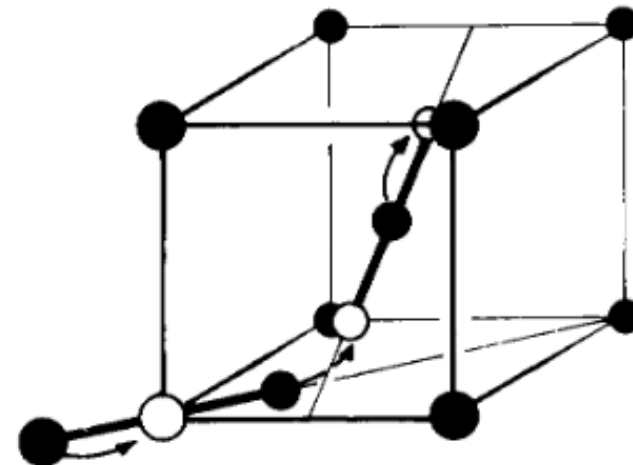
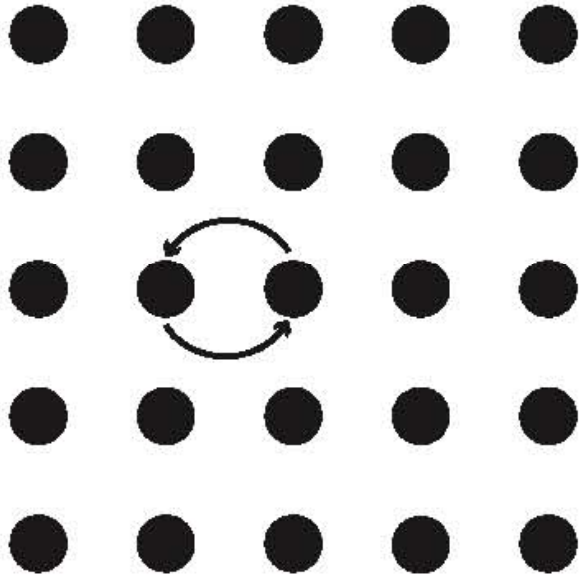


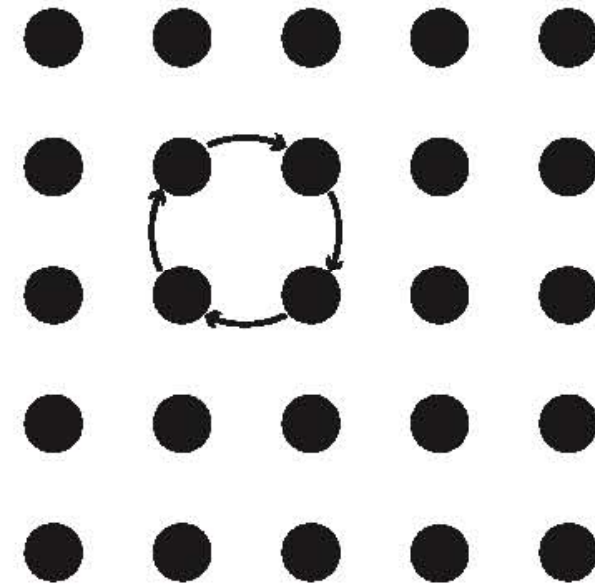
Fig. 9. Migration of the (110)-split interstitial in a bcc lattice.

Mechanisms of Diffusion

Exchange Mechanism

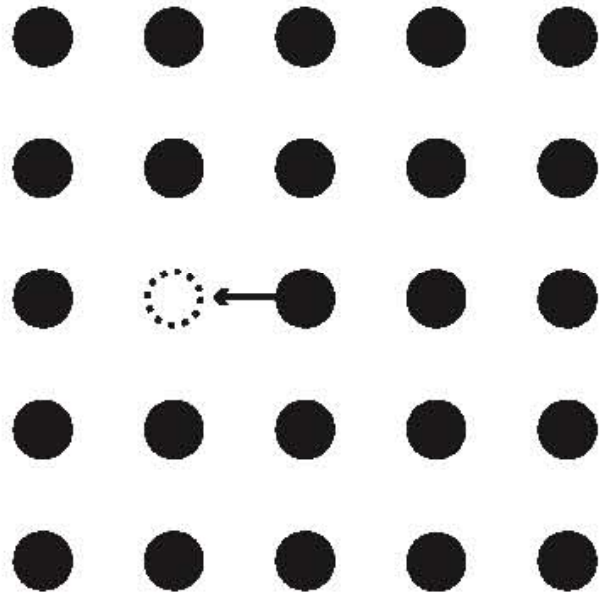


Ring Mechanism

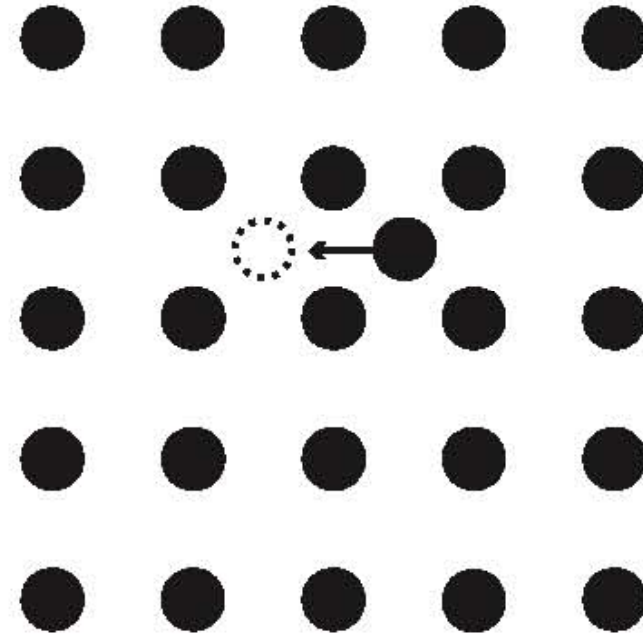


Mechanisms of Diffusion

Vacancy Mechanism

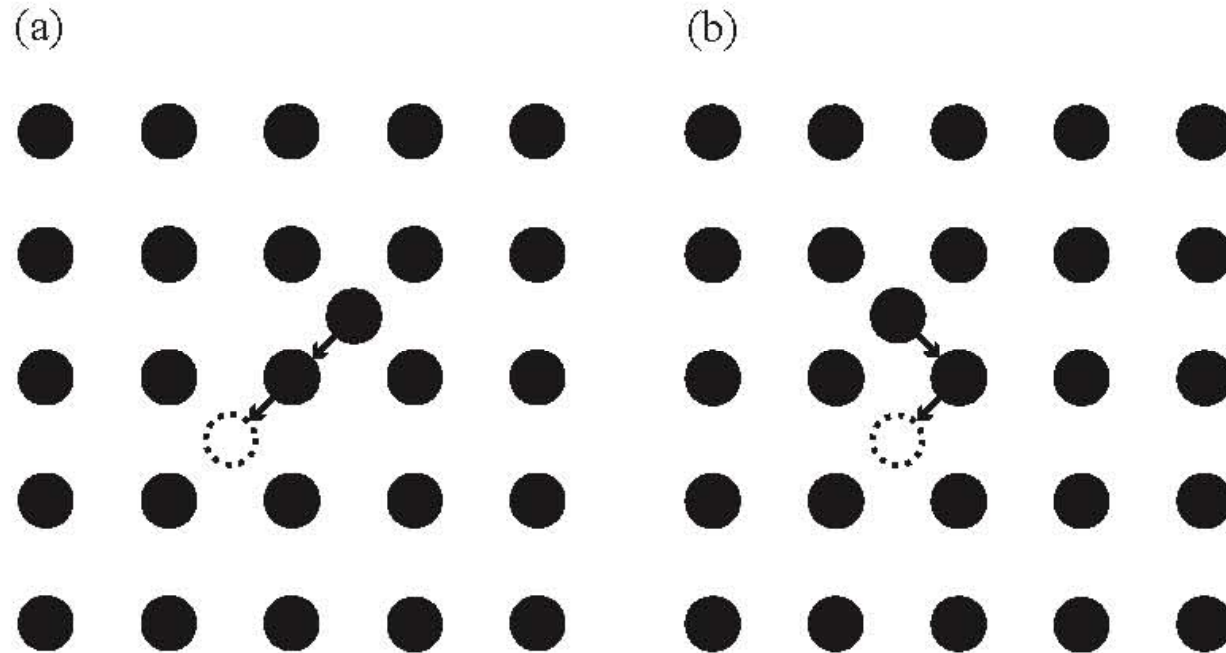


Interstitial Mechanism



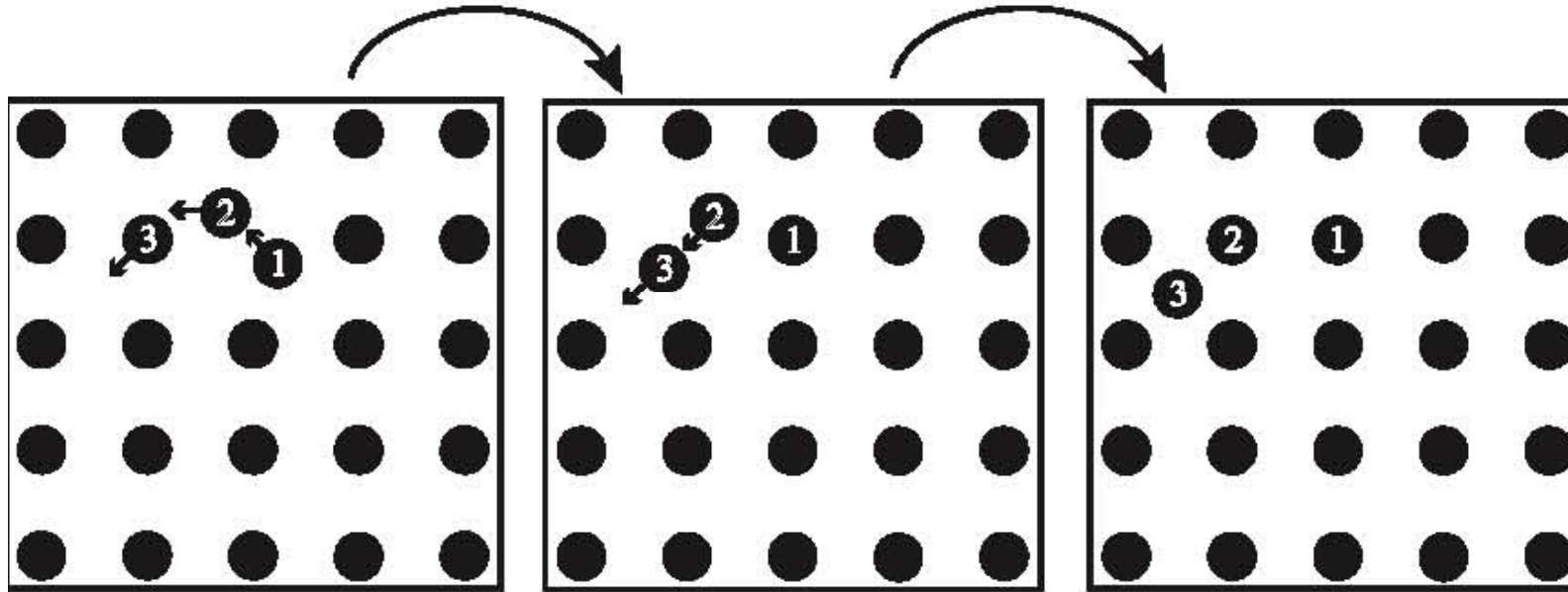
Mechanisms of Diffusion

Interstitialcy Mechanism



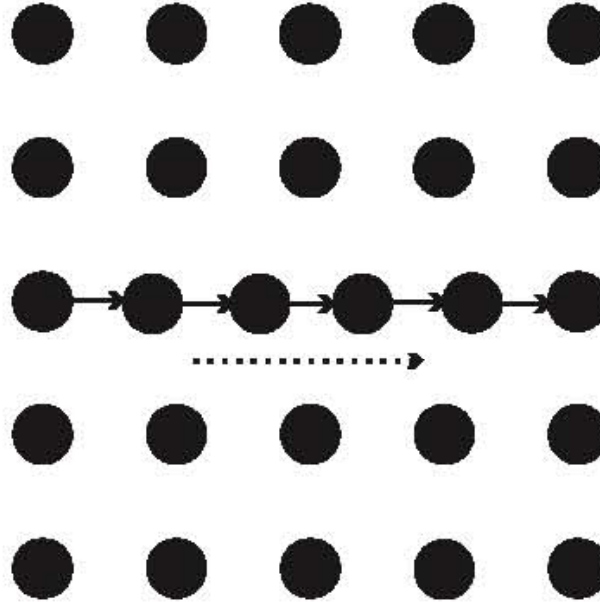
Mechanisms of Diffusion

Dumbbell Mechanism



Mechanisms of Diffusion

Crowdion mechanism



Poll – what mechanism(s) is most dominant

- A.Exchange
- B.Ring
- C.Vacancy
- D.Interstitial
- E.Interstitialcy
- F.Dumbbell
- G.Crowdion



The Singapore Grand Prix is F1's first night race. To improve visibility how many light projectors are there around the track?



Microscopic Diffusion

- Assume that the self-diffusion process consists of a completely random walk of defects
- Assume steps of equal length, random directions:

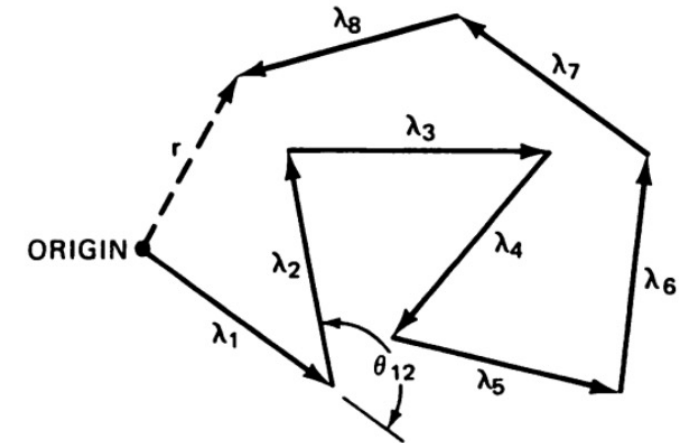


Fig. 7.4 Eight random jumps of equal length λ .

Microscopic Diffusion

$$\bar{r}^2 = n\lambda^2$$

We need to now convert this to a function of time, t . We can do this by considering the frequency of each jump, Γ , and the time allowed for hopping, then we get:

We now need to equate this to the [macroscopic](#) diffusion, D . To do this we use Ficks second law of diffusion to describe the probability of finding a spherical shell surrounding an origin:

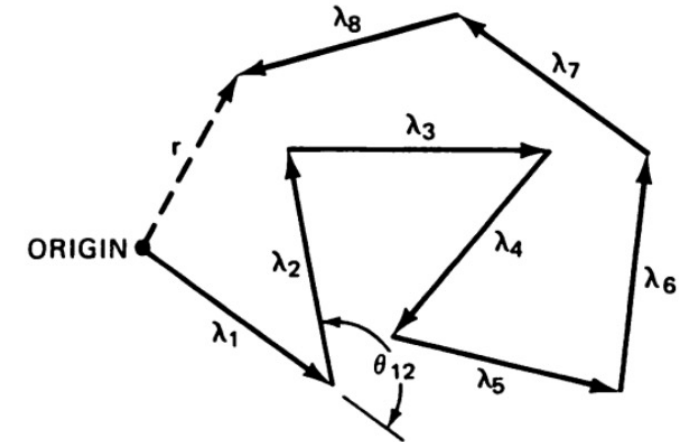


Fig. 7.4 Eight random jumps of equal length λ .



Microscopic Diffusion

Both the **macroscopic** and **microscopic** equations can be equated together based on both can be defined based on the probability, p_t . To do this, we substitute $p_t(r)$ into:

$$\bar{r}^2 = 4\pi \int_0^\infty r^4 p_t(r) dr$$

And solving, we get simply:

$$\bar{r}^2 = 6Dt$$

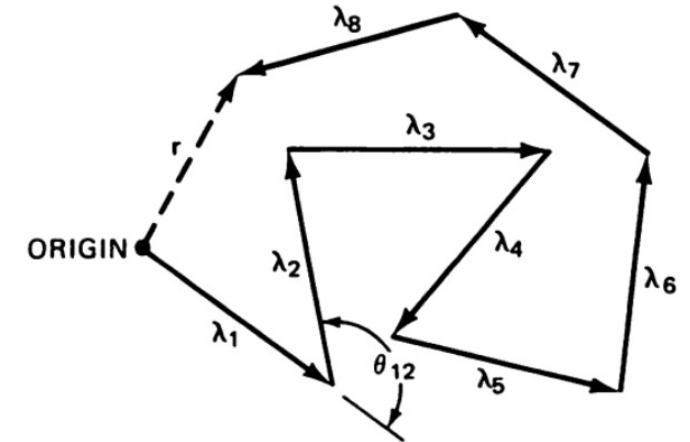


Fig. 7.4 Eight random jumps of equal length λ .

Diffusion accounting for hopping mechanism

Knowing now that:

$$D = \frac{1}{6} \lambda^2 \Gamma$$

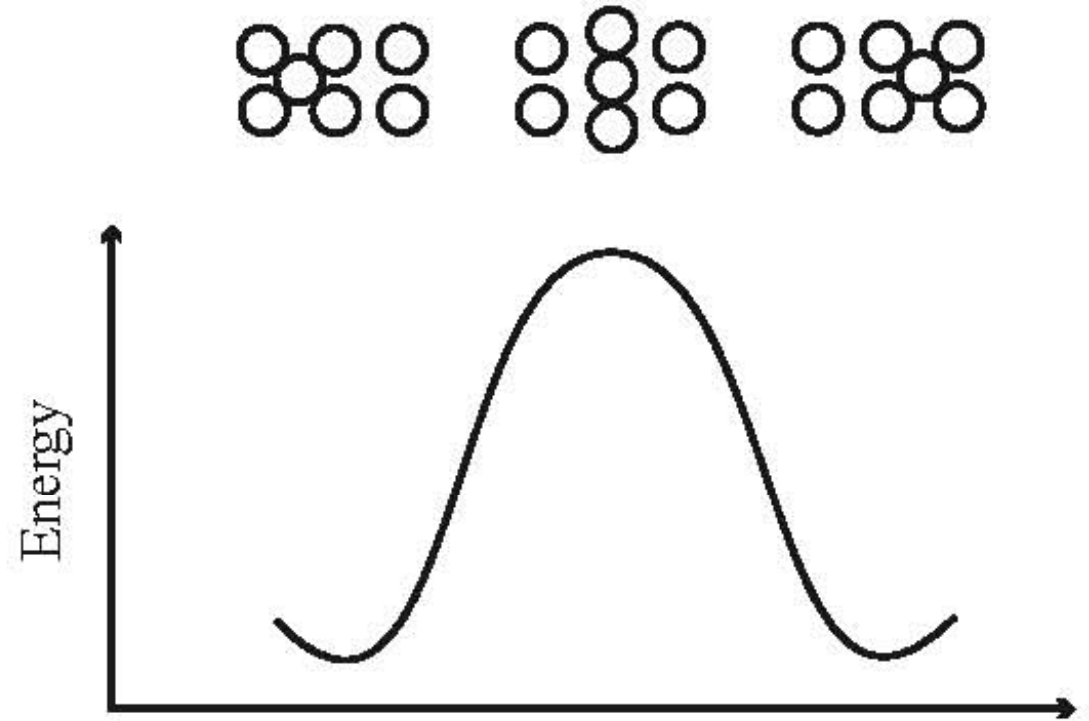
We need to determine the jump frequency for a given jump mechanism. This is dependent on the probability a jump site is open, ρ_j , the number of nearest neighbors, z , and the frequency of a given jump type, ω :

How to determine ω

$$\omega = v \exp\left(\frac{-\Delta G_m}{k_b T}\right)$$

$$\omega = v \exp\left(\frac{-S_m}{k_b}\right) \exp\left(\frac{-\Delta H_m}{k_b T}\right)$$

$$\omega = v \exp\left(\frac{-S_m}{k_b}\right) \exp\left(\frac{-\Delta E_m}{k_b T}\right)$$



Pulling it together to get the diffusion equations:

Diffusion of vacancies:

$$D_v = \alpha a^2 \omega = \alpha a^2 v \exp\left(\frac{S_m^v}{k}\right) \exp\left(\frac{-E_m^v}{kT}\right)$$

Diffusion of atoms by way of vacancies – vacancy self-diffusion:

$$D_a^v = \alpha a^2 v \exp\left(\frac{S_f^v + S_m^v}{k}\right) \exp\left(\frac{-E_f^v - E_m^v}{kT}\right).$$

Diffusion of interstitials:

$$D_i = \alpha a^2 v \exp\left(\frac{S_m^i}{k}\right) \exp\left(\frac{-E_m^i}{kT}\right).$$

Diffusion of atoms by way of interstitials – interstitial self-diffusion:

$$D_a^i = \alpha a^2 v \exp\left(\frac{S_f^i + S_m^i}{k}\right) \exp\left(\frac{-E_f^i + -E_m^i}{kT}\right).$$

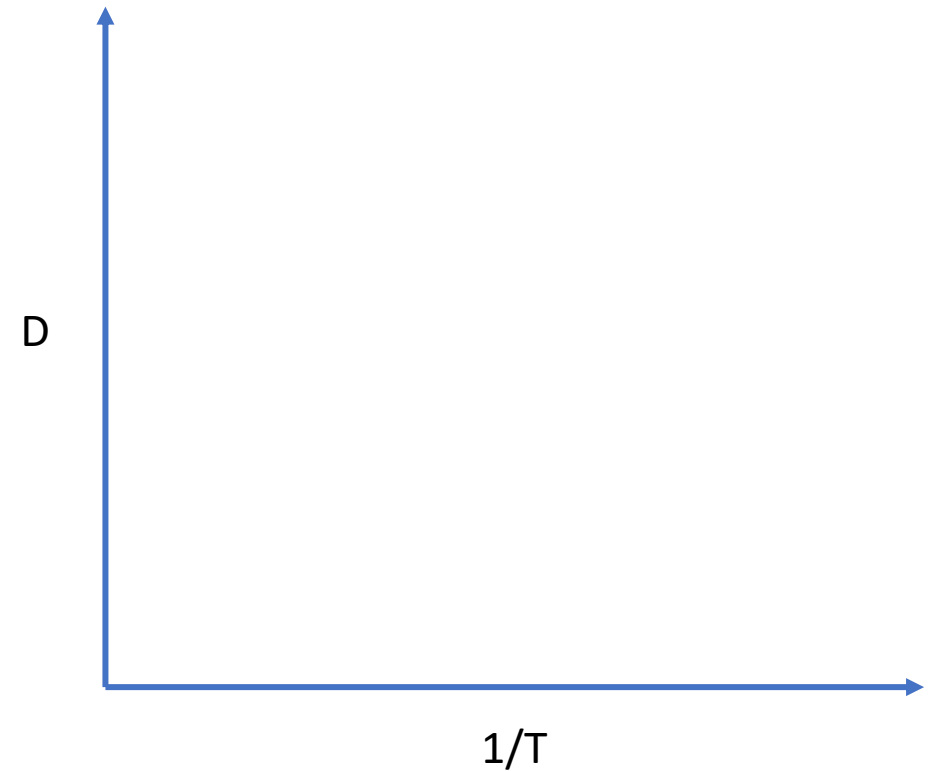


Or, more simply:

We can use an Arrhenius relationship:

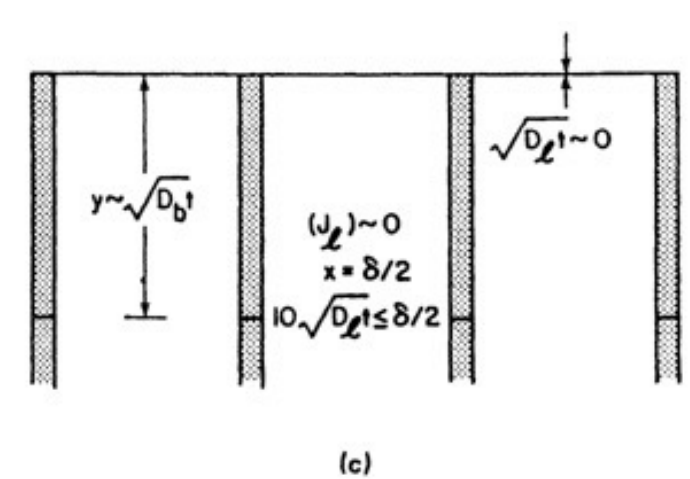
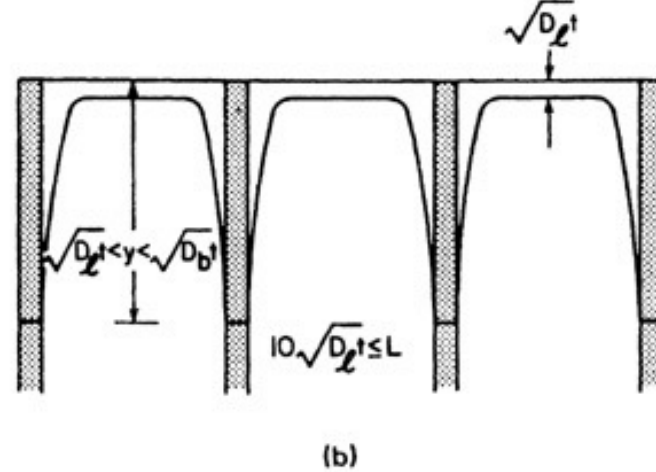
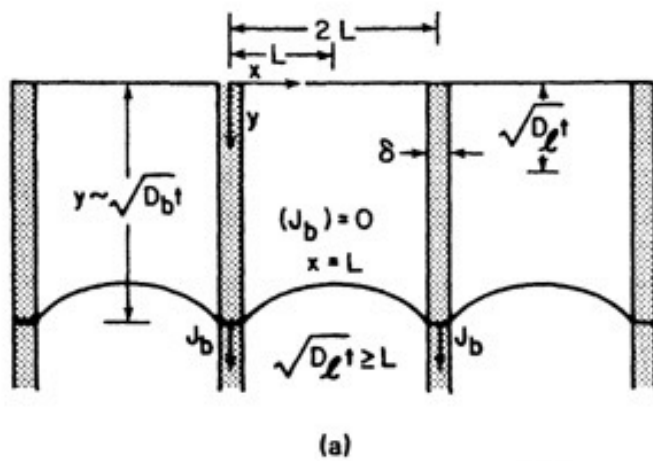
$$D = D_0 \exp\left(-Q/k_b T\right)$$

Where D_0 and Q are given but incorporate the discussed factors:



Mechanism	D_0	Q
Vacancy Diffusion (D_v)	$\alpha a_o^2 v \exp\left(\frac{S_m^v}{k_b}\right)$	E_m^v
Vacancy Self Diffusion (D_a^v)	$\alpha a_o^2 v \exp\left(\frac{S_f^v + S_m^v}{k_b}\right)$	$E_f^v + E_m^v$

Diffusion along high-diffusivity paths:



Type A: The diffusion front in the bulk and in the boundary advanced at the same speed

Type B: The diffusion in the grain boundary is faster than in the bulk

Type C: The diffusion in the bulk is negligible and grain boundary diffusion is only active

Point defect properties

	Symbol	Unit	Al	Cu	Pt	Mo	W
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Formation energy	E_f^{FP}	eV	3.9	3.5	5		

Point Defect Diffusion: Comparison

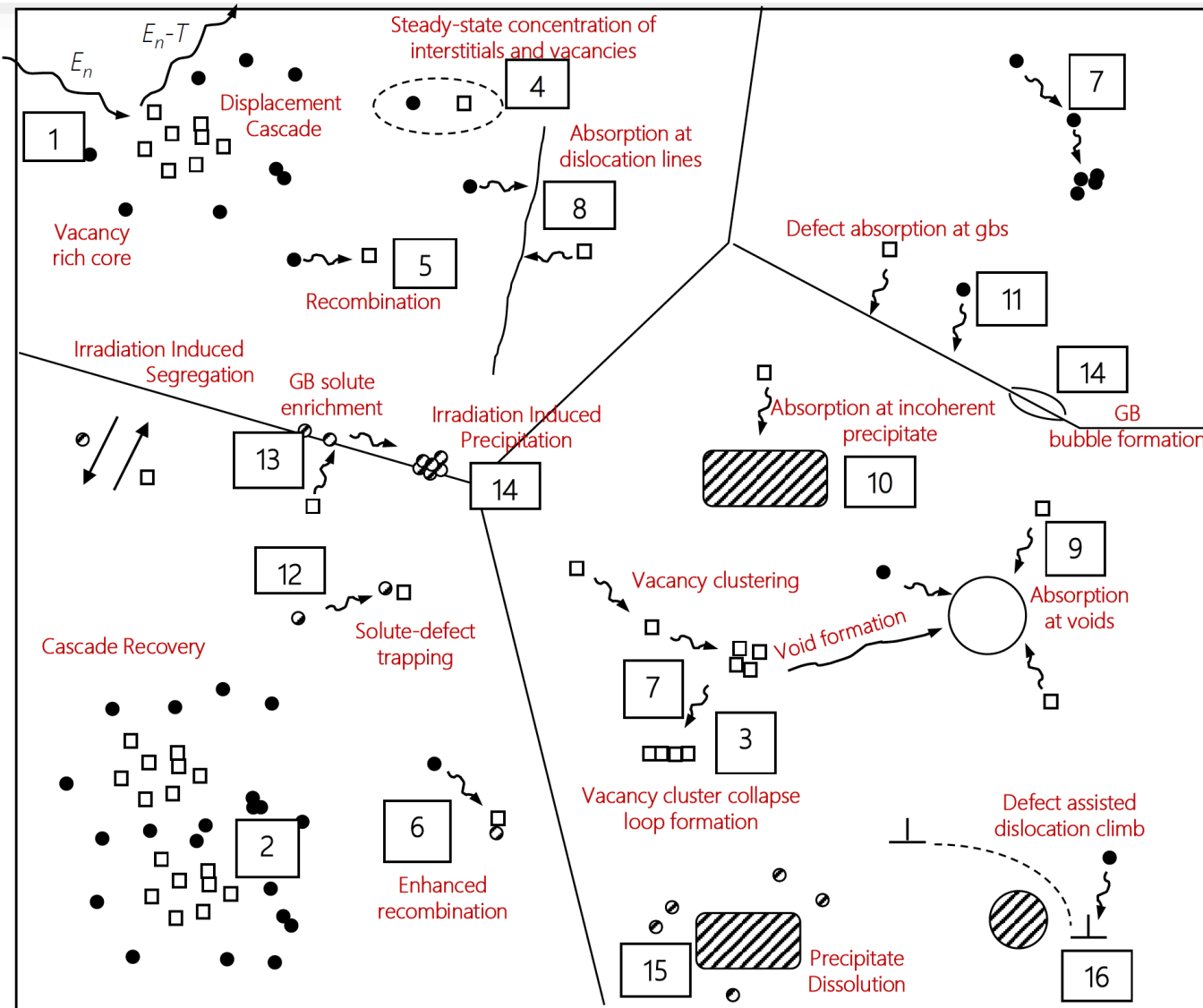
- Comparison of diffusion
 - $t = 10^6 \text{ s}$ (11 days)
 - $E_m^f = 1 \text{ eV}$, $E_m^i = 0.2 \text{ eV}$

T (°C)	$D_V(\text{m}^2/\text{s})$	$X_V = \sqrt{D_V \tau}$	$D_i(\text{m}^2/\text{s})$	$X_i = \sqrt{D_i \tau}$
0	2×10^{-21}	0.45nm	1.5×10^{-6}	1cm
100	2×10^{-16}	150nm	1.5×10^{-5}	4cm
200	1.7×10^{-13}	4 μm	5.5×10^{-5}	7.5cm
300	1.2×10^{-11}	35 μm	1.3×10^{-4}	11cm
400	2.5×10^{-10}	0.15mm	2.4×10^{-4}	15cm
500	2.3×10^{-9}	4mm	3.7×10^{-4}	19cm



Radiation Effects at the Grain Scale

Goal: Determine the kinetics of microstructure evolution under irradiation



Questions?

